

*CLAIM AMENDMENTS*

1. (Currently Amended) A method~~for~~ of manufacturing a buried wiring structure comprising:  
depositing an insulating film on under-layer wiring;  
forming a first depressed portion in~~an~~ the insulating film;  
applying a burying material to the first depressed portion and on said insulating film, filling the first depressed portion;  
chemical mechanical polishing the burying material until the insulating film is exposed, leaving the burying material in the first depressed portion;  
forming a resist having a pattern of a second depressed portion that overlaps the first depressed portion on the insulating film where the burying material is present;  
etching the burying material and the insulating film, using the resist as a mask, to form the second depressed portion;  
removing the resist and the burying material left after the etching; and  
depositing an electrically conductive material in the first depressed portion and the second depressed portion.

Claims 2 and 3 (Cancelled)

4. (Currently Amended) The method~~for~~ of manufacturing a buried wiring structure according to claim ~~2~~1, including applying as the burying material an organic polymeric material having substantially the same etching rate as the insulating film.

5. (Currently Amended) The method~~for~~ of manufacturing a buried wiring structure according to claim 1, including applying as the burying material an organic polymeric material containing no aromatic compounds.

6. (Currently Amended) The method~~for~~ of manufacturing a buried wiring structure according to claim 5, further comprising forming an antireflective film on the insulating film before forming the resist.

7. (Currently Amended) The method~~for~~ of manufacturing a buried wiring structure according to claim 6, wherein the burying material and the antireflective film are not soluble in each other.

- In re Appln. of ISHIBASHI et al.  
Application No. 10/619,433

8. (New) The method of manufacturing a buried wiring structure according to claim 1, wherein the first depressed portion is a contact hole and the second depressed portion is a wiring channel, the contact hole being deeper and narrower than the wiring channel.

9. (New) The method of manufacturing a buried wiring structure according to claim 1, wherein the first depressed portion is a wiring channel and the second depressed portion is a contact hole, the contact hole being deeper and narrower than the wiring channel.